

Product data sheet

## 1. General description

Hyperfast power diode in a SOT429 (3-lead TO247) plastic package.

## 2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

## 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 115 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	30	A
Static chara	cteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.38	1.8	V
Dynamic ch	aracteristics	·	1				
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	18	22	ns





## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		K – K – A
2	К	cathode		001aaa020
3	А	anode		
mb	mb	mounting base; connected to cathode	TO-247 (SOT429)	

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYC30WT-600P	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429				

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC30WT-600P	BYC30WT-600P

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	30	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; square-wave pulse	-	60	А

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# BYC30WT-600P

#### Hyperfast power diode

Symbol	Parameter	Conditions	IV	lin	Max	Unit
	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-		270	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-		300	A
T <sub>stg</sub>	storage temperature		-1	65	175	°C
Tj	junction temperature		-		175	°C

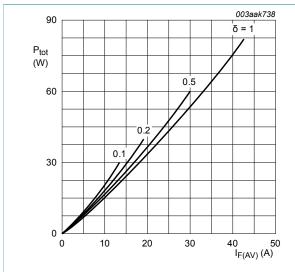
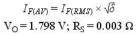
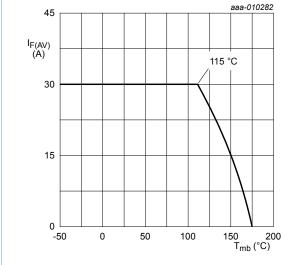
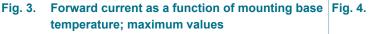


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values







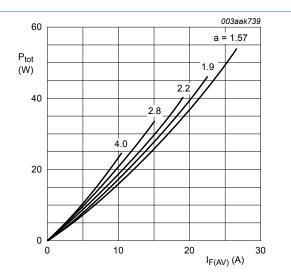
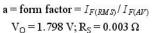
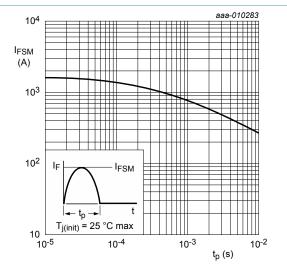


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



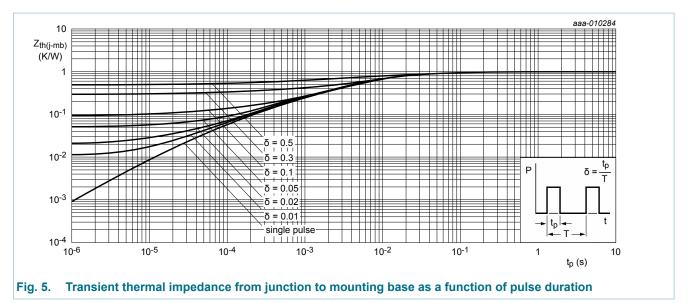


4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Hyperfast power diode

## 9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	45	-	K/W



## **10. Characteristics**

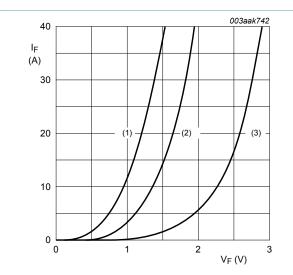
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		·			
V <sub>F</sub> forward voltage		I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I <sub>R</sub> reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA	
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	1	mA
Dynamic cl	naracteristics		I			
Q <sub>r</sub> recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	50	-	nC	
		$I_F$ = 30 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 125 °C; <u>Fig. 7</u>	-	280	-	nC

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# BYC30WT-600P

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 200 A/µs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	18	22	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	35	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	70	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/ μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	29	-	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	3.5	-	A
		$I_F$ = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	7.6	-	A





 (1) T<sub>j</sub> = 150 °C; typical values;
(2) T<sub>j</sub> = 150 °C; maximum values;
(3) T<sub>j</sub> = 25 °C; maximum values; V<sub>O</sub> = 1.798 V; R<sub>S</sub> = 0.003 Ω

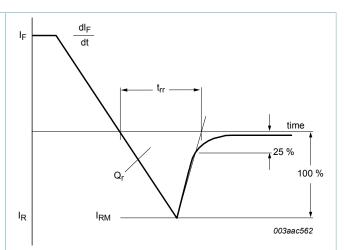
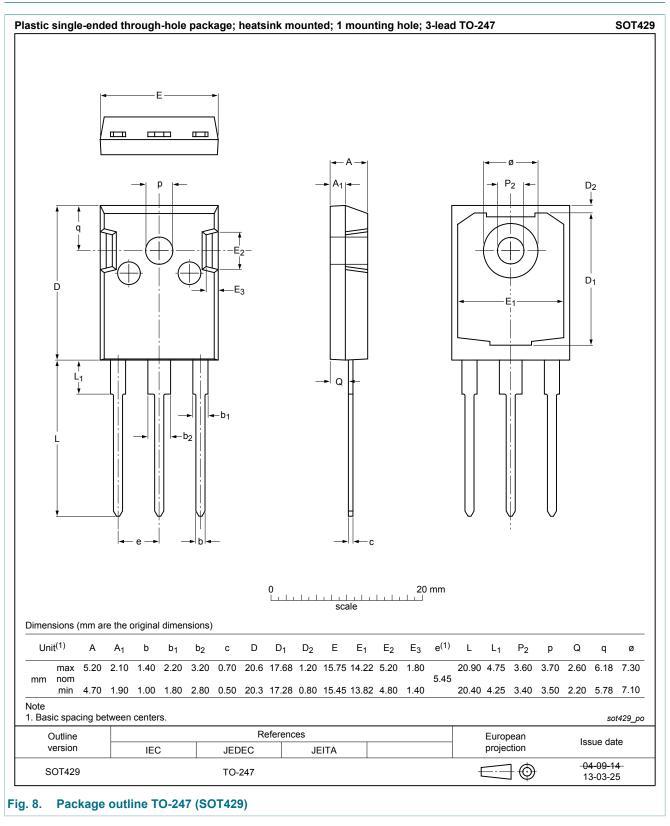


Fig. 7. Reverse recovery definitions; ramp recovery



### **11. Package outline**



#### Hyperfast power diode

### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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